MITSUBISHI SEMICONDUCTOR <GaAs FET>

MGFC36V7785A

7.7 ~ 8.5GHz BAND 4W INTERNALLY MATCHED GaAs FET

DESCRIPTION

The MGFC36V7785A is an internally impedance-matched GaAs power FET especially designed for use in 7.7 ~ 8.5 GHz band amplifiers. The hermetically sealed metal-ceramic package guarantees high reliability.

FEATURES

Class A operation Internally matched to 50(ohm) system High output power P1dB = 4W (TYP.) @ f=7.7~8.5GHz High power gain GLP = 8 dB (TYP.) @ f=7.7~8.5GHz High power added efficiency P.A.E. = 29 % (TYP.) @ f=7.7~8.5GHz Low distortion [item -51] IM3= -45 dBc(TYP.) @ Po=25dBm S.C.L.

APPLICATION

item 01 : 7.7~8.5 GHz band power amplifier item 51 : 7.7~8.5 GHz band digital radio communication

QUALITY GRADE

IG

RECOMMENDED BIAS CONDITIONS

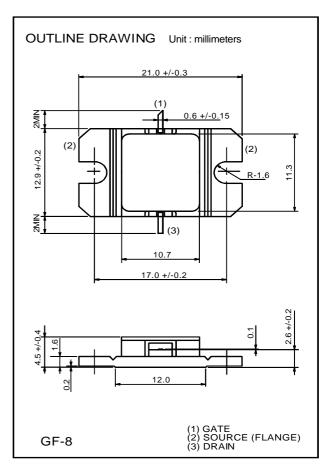
VDS = 10 (V)ID = 1.2 (A) Refer to Bias Procedure RG= 100 (ohm)

ABSOLUTE MAXIMUM RATINGS (Ta=25 deg.C)

			0,	
Symbol	Parameter	Ratings	Unit	
VGDO	Gate to drain voltage	-15	V	
VGSO	Gate to source voltage	-15	V	
ID	Drain current	3.75	Α	
IGR	Reverse gate current	-10	mA	
IGF	Forward gate current	21	mA	
PT	Total power dissipation *1	25	W	
Tch	Channel temperature	175	deg.C	
Tstg	Storage temperature	-65 / +175	deg.C	



ELECTRICAL CHARACTERISTICS



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Symbol	Parameter	Test conditions	Limits			Unit		
Symbol			Min.	Тур.	Max.	Unit		
IDSS	Saturated drain current	VDS=3V, VGS=0V	-	-	3.75	Α		
gm	Transconductance	VDS=3V, ID=1.1A	-	1	-	S		
VGS(off)	Gate to source cut-off voltage	VDS=3V, ID=10mA	-	-	-4.5	V		
P1dB	Output power at 1dB gain compression	1	35	36.5	-	dBm		
GLP	Linear power gain	VDS=10V, ID(RF off)=1.2A, f=7.7~8.5GHz	7	8	-	dB		
ID	Drain current		-	-	1.8	Α		
P.A.E.	Power added efficiency		-	29	-	%		
IM3	3rd order IM distortion *1		-42	-45	-	dBc		
Rth(ch-c)	Thermal resistance *2	Delta Vf method	-	5	6	deg.C/W		
*1 : item -51, 2 tone test, Po=25dBm Single Carrier Level, f=8 5GHz, Delta f=10MHz								

(Ta=25 deg.C)

*1 : item -51, 2 tone test, Po=25dBm Single Carrier Level, f=8.5GHz, Delta f=10MHz

*2 : Channel to case



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